

L Number	Hits	Search Text	DB	Time stamp
1	93	((ion adj implant) near (silicon near2 (substrate or wafer)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/07 21:33
2	2762	((438/245) or (438/246) or (438/360) or (438/361) or (438/388) or (438/389) or (438/407) or (438/409) or (438/411) or (438/421) or (438/423) or (438/424) or (438/429) or (438/430) or (438/431) or (438/432) or (438/524)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/07 21:28
3	2	((ion adj implant) near (silicon near2 (substrate or wafer))) and (((438/245) or (438/246) or (438/360) or (438/361) or (438/388) or (438/389) or (438/407) or (438/409) or (438/411) or (438/421) or (438/423) or (438/424) or (438/429) or (438/430) or (438/431) or (438/432) or (438/524)).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/07 21:28
-	2743	((438/245) or (438/246) or (438/360) or (438/361) or (438/388) or (438/389) or (438/407) or (438/409) or (438/411) or (438/421) or (438/423) or (438/424) or (438/429) or (438/430) or (438/431) or (438/432) or (438/524)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/07 21:28
-	78084	air near2 gap	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/19 17:15
-	75478	trench or trenches	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/19 17:15
-	13219	anodize or anodizing	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/19 17:15
-	5398	porous near2 silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/19 17:21
-	271	(air near2 gap) same (trench or trenches)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/19 17:16
-	5	((air near2 gap) same (trench or trenches)) and (anodize or anodizing)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/19 17:16
-	4	((air near2 gap) same (trench or trenches)) and (anodize or anodizing)) and (porous near2 silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/19 17:17
-	15	((((438/245) or (438/246) or (438/360) or (438/361) or (438/388) or (438/389) or (438/407) or (438/409) or (438/411) or (438/421) or (438/423) or (438/424) or (438/429) or (438/430) or (438/431) or (438/432) or (438/524)).CCLS.) and (air near2 gap)) and (porous near2 silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/19 17:20

-	1	((((438/245) or (438/246) or (438/360) or (438/361) or (438/388) or (438/389) or (438/407) or (438/409) or (438/411) or (438/421) or (438/423) or (438/424) or (438/429) or (438/430) or (438/431) or (438/432) or (438/524)).CCLS.) and (air near2 gap)) and (anodize or anodizing)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/19 17:20
-	4262	porous near silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/19 17:21
-	374724	porous	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/19 17:21
-	94	((((438/245) or (438/246) or (438/360) or (438/361) or (438/388) or (438/389) or (438/407) or (438/409) or (438/411) or (438/421) or (438/423) or (438/424) or (438/429) or (438/430) or (438/431) or (438/432) or (438/524)).CCLS.) and (air near2 gap)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/19 17:34
-	1	6406975.URPN.	USPAT	2003/12/19 17:25
-	13	("4994404" "5098856" "5387538" "5508234" "5559367" "5830332" "5953626" "6001705" "6004863" "6004864" "6071805" "6127241" "6130102").PN.	USPAT	2003/12/19 17:29
-	14619	sti or (shallow near2 trench)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/19 17:34
-	6	(sti or (shallow near2 trench)) near (air near2 gap)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/19 17:35
-	20	(sti or (shallow near2 trench)) same (air near2 gap)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/19 17:35